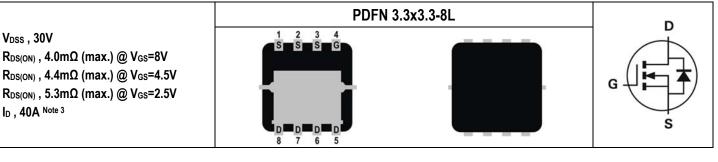


# SG30N06LE

30V N-Channel Power MOSFET



| Description  | Features  |
|--|---|
| The SG30N06LE uses advanced Trench technology and designs to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications. | <ul> <li>Low On-Resistance</li> <li>Low Input Capacitance</li> <li>Low Miller Charge</li> <li>Low Input / Output Leakage</li> <li>Pb-free lead plating; RoHS compliant</li> </ul> |
|  | Applications  |
|  | <ul> <li>Lithium-Ion Secondary Batteries</li> <li>Notebook PCs</li> <li>Load Switch</li> <li>DC-DC converters and Off-line UPS</li> </ul>   |

#### **Ordering Information**

| Ordering Code | RoHS Status  | Package         | Package Code | Packing     | Quantity |
|---------------|--------------|-----------------|--------------|-------------|----------|
| SG30N06LE     | Halogen-Free | PDFN 3.3x3.3-8L | E            | Tape & Reel | 5,000    |

## Absolute Maximum Ratings (TA=25°C unless otherwise noted)

| Parameter                            |                      | Symbol          | Value       | Unit |
|--------------------------------------|----------------------|-----------------|-------------|------|
| Drain-Source Voltage                 |                      | V <sub>DS</sub> | 30          | V    |
| Gate-Source Voltage                  |                      | Vgs             | +10/-8      | V    |
| Drain Current-Continuous Note 3      | Tc=25°C              | 1-              | 40          | Α    |
| Drain Current-Continuous Notes       | T <sub>C</sub> =70°C | lD ID           | 40          | A    |
| Drain Current-Pulsed Note 1          | ·                    | Ідм             | 100         | Α    |
| Drain Current Centinuous             | T <sub>A</sub> =25°C |                 | 25          | Α    |
| Drain Current-Continuous             | T <sub>A</sub> =70°C |                 | 20          | Α    |
| Avalanche Current, L=0.1mH           | ·                    | las             | 38          | Α    |
| Avalanche Energy, L=0.1mH            |                      | Eas             | 72          | mJ   |
|                                      | T <sub>c</sub> =25°C |                 | 52          | W    |
| Maximum Dawar Disaination            | Tc=70°C              |                 | 33          | W    |
| Maximum Power Dissipation            | T <sub>A</sub> =25°C |                 | 3.8         | W    |
|                                      | T <sub>A</sub> =70°C |                 | 2.4         | W    |
| Operating Junction Temperature Range | ·                    | TJ TSTG         | -55 to +150 | °C   |

#### **Thermal Resistance Ratings**

| Parameter                   | Symbol | Conditions   | Min. | Тур. | Max. | Unit |
|-----------------------------|--------|--------------|------|------|------|------|
| Maximum Junction-to-Ambient | Reja   | t ≤ 10s      | -    | -    | 33   | °C/W |
| Maximum Junction-to-Case    | Rejc   | Steady State | -    | -    | 2.4  | °C/W |



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#### Electrical Characteristics (T\_=25°C unless otherwise noted)

| OFF CHARACTERISTICS             |                   |   |      |      |      |      |
|---------------------------------|-------------------|---|------|------|------|------|
| Parameter                       | Symbol            | Conditions                                    | Min. | Тур. | Max. | Unit |
| Drain-Source Breakdown Voltage  | BV <sub>DSS</sub> | V <sub>GS</sub> =0V, I <sub>DS</sub> =250µA   | 30   | -    | -    | V    |
| Zero Gate Voltage Drain Current | IDSS              | V <sub>DS</sub> =30V, V <sub>GS</sub> =0V     | -    | -    | 1    | μA   |
| Gate-Body Leakage               | lgss              | V <sub>GS</sub> =+10/-8V, V <sub>DS</sub> =0V | -    | -    | ±100 | nA   |

| ON CHARACTERISTICS               |                        |   |      |      |      |      |
|----------------------------------|------------------------|---|------|------|------|------|
| Parameter                        | Symbol                 | Conditions  | Min. | Тур. | Max. | Unit |
| Gate Threshold Voltage           | V <sub>GS(TH)</sub>    | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250µA | 0.6  | -    | 1.1  | V    |
| Drain-Source On-State Resistance |                        | V <sub>GS</sub> =8V, I <sub>DS</sub> =20A                 | -    | -    | 4.0  | mΩ   |
| Drain-Source On-State Resistance | RDS(ON)                | V <sub>GS</sub> =4.5V, I <sub>DS</sub> =20A               | -    | -    | 4.4  | mΩ   |
| Drain-Source On-State Resistance |                        | V <sub>GS</sub> =2.5V, I <sub>DS</sub> =20A               | -    | -    | 5.3  | mΩ   |
| Forward Transconductance Note 1  | <b>g</b> <sub>fs</sub> | V <sub>DS</sub> =15V, I <sub>D</sub> =20A                 | -    | 82   | -    | S    |

| DYNAMIC CHARACTERISTICS      |        |   |      |      |      |      |  |
|------------------------------|--------|---|------|------|------|------|--|
| Parameter                    | Symbol | Conditions  | Min. | Тур. | Max. | Unit |  |
| Input Capacitance            | Ciss   |   | -    | 1666 | 2065 |      |  |
| Output Capacitance           | Coss   | V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz | -    | 342  | 434  | pF   |  |
| Reverse Transfer Capacitance | Crss   |   | -    | 142  | 174  |      |  |
| Gate Resistance              | Rg     | V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz  | -    | 3    | 4    | Ω    |  |

| SWITCHING CHARACTERISTICS     |                     |  |      |      |      |      |
|-------------------------------|---------------------|--|------|------|------|------|
| Parameter                     | Symbol              | Conditions   | Min. | Тур. | Max. | Unit |
| Turn-On Delay Time            | T <sub>d(on)</sub>  |  | -    | 23   | -    |      |
| Rise Time                     | tr                  | V <sub>DD</sub> =15V, I <sub>D</sub> =10A, V <sub>GEN</sub> =4.5V, | -    | 20   | -    |      |
| Turn-Off Delay Time           | T <sub>d(off)</sub> | $R_{GEN}=1\Omega$ , $R_{L}=1.5\Omega$                              | -    | 24   | -    | ns   |
| Fall Time                     | tr                  |  | -    | 16   | -    |      |
| Total Gate Charge at 10V      | Qg                  |  | -    | 11   | 16.5 |      |
| Gate to Source Gate Charge    | Qgs                 | V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =19A   | -    | 5    | -    | nC   |
| Gate to Drain "Miller" Charge | Q <sub>gd</sub>     |  | -    | 4    | -    |      |

| DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS |        |   |      |      |      |      |
|--|--------|---|------|------|------|------|
| Parameter  | Symbol | Conditions                              | Min. | Тур. | Max. | Unit |
| Maximum Body-Diode Continuous Current                  | ls     | -                                       | -    | -    | 40   | Α    |
| Drain-Source Diode Forward Voltage                     | Vsd    | V <sub>GS</sub> =0V, I <sub>S</sub> =1A | -    | 0.8  | 1.2  | V    |
| Body Diode Reverse Recovery Time                       | trr    | I⊧=10A, dl/dt=100A/µs, Tյ=25°C          | -    | 24   | -    | ns   |
| Body Diode Reverse Recovery Charge                     | Qrr    | 1F = 10A, ui/ul = 100A/µS, 1J=25 C      | -    | 16   | -    | nC   |

Notes:

1. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

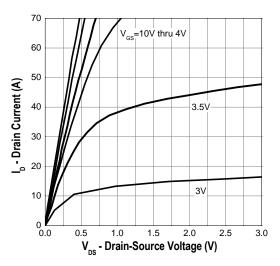
 R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>BJC</sub> is guaranteed by design while R<sub>BJA</sub> is determined by the user's board design. R<sub>BJA</sub> shown below for single device operation on FR-4 in still air.

3. The maximum current rating is limited by package.

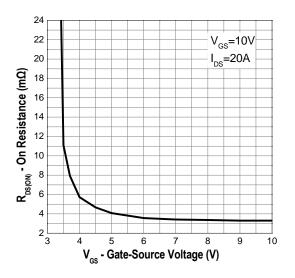


## **Typical Operating Characteristics**

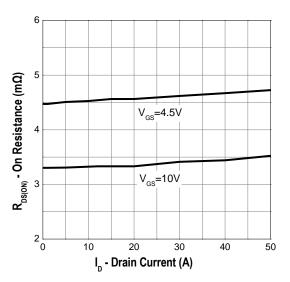
#### **Output Characteristics**



**Gate-Source On Resistance** 



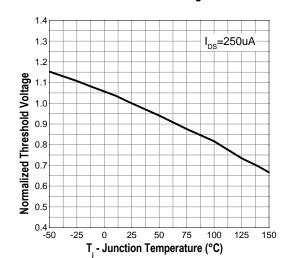
**Drain-Source On Resistance** 



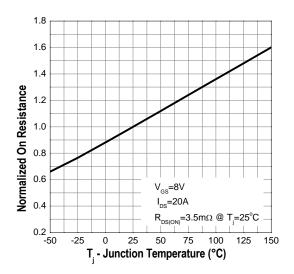
#### Gate Threshold Voltage

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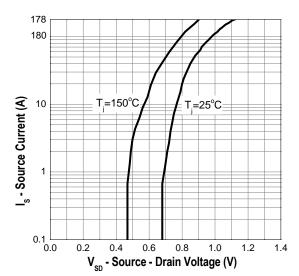
30V N-Channel Power MOSFET



**Drain-Source On Resistance** 



Source-Drain Diode Forward

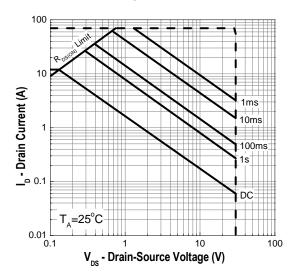




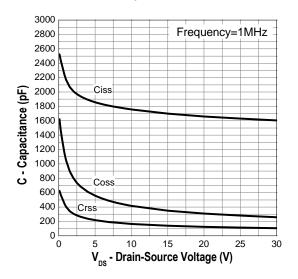
## **Typical Operating Characteristics (Cont.)**

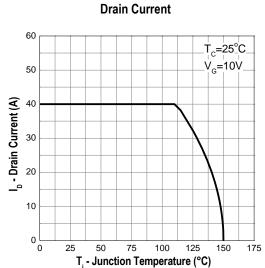
#### **Power Dissipation** 50 T\_=25°C 40 P<sub>tot</sub> - Power (W) 30 20 10 0 L 0 25 50 75 100 125 150 175 T<sub>i</sub> - Junction Temperature (°C)

Safe Operation Area



Capacitance

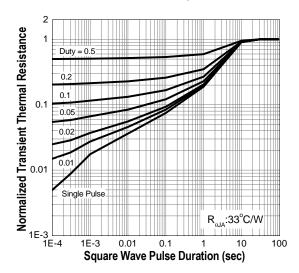




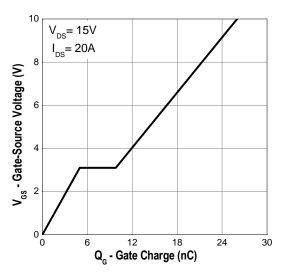
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**Transient Thermal Impedance** 







Drain Curr



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## **Marking Information**

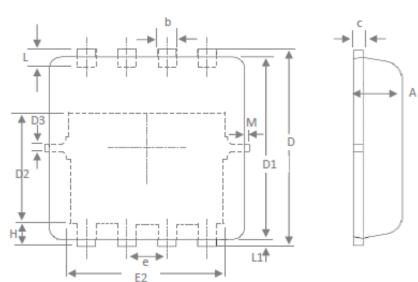
| PDFN 3.3x3.3-8L (E)                          | Marking Rule  |
|--|---|
| Laser Marking<br>30N06L<br>YMMXXX<br>Diagram | Line 1 : Device Name<br>30N06L<br>Line 2 : Date Code<br>YMMXXX<br>Y : Year Code<br>MM : Month Code<br>XXX : Serial Number<br>Year Code Description As Below |

## Year Code Description

| Year Code | Ye   | ear  |
|-----------|------|------|
| 0         | 2010 | 2020 |
| 1         | 2011 | 2021 |
| 2         | 2012 | 2022 |
| 3         | 2013 | 2023 |
| 4         | 2014 | 2024 |
| 5         | 2015 | 2025 |
| 6         | 2016 | 2026 |
| 7         | 2017 | 2027 |
| 8         | 2018 | 2028 |
| 9         | 2019 | 2029 |



## Package of Dimension



| Symbol | Min  | Nor     | Max  |
|--------|------|---------|------|
| Α      | 0.70 | 0.75    | 0.80 |
| b      | 0.25 | 0.30    | 0.35 |
| с      | 0.10 | 0.15    | 0.25 |
| D      | 3.25 | 3.35    | 3.45 |
| D1     | 3.00 | 3.10    | 3.20 |
| D2     | 1.78 | 1.88    | 1.98 |
| D3     | -    | 0.13    | -    |
| E      | 3.00 | 3.30    | 3.40 |
| E1     | 3.00 | 3.15    | 3.20 |
| E2     | 2.39 | 2.49    | 2.59 |
| е      |      | 0.65BSC |      |
| Н      | 0.30 | 0.39    | 0.50 |
| L      | 0.30 | 0.40    | 0.50 |
| L1     | -    | 0.13    | -    |
| θ      | -    | 10°     | 12°  |
| М      |      |         | 0.15 |



Note:

- 1. All Dimension Are In mm.
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.

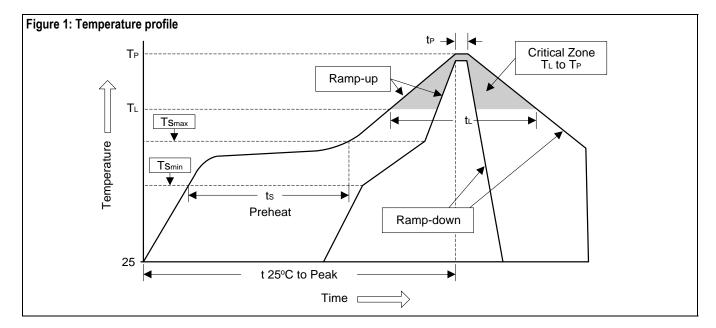
SG30N06LE 30V N-Channel Power MOSFET





#### **Soldering Methods for Silicongear's Products**

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



| Profile Feature                              | Sn-Pb Eutectic Assembly | Pb-Free Assembly |
|--|-------------------------|------------------|
| Average ramp-up rate $(T_L \text{ to } T_P)$ | <3°C/sec                | <3°C/sec         |
| Preheat                                      |                         |                  |
| - Temperature Min (Ts <sub>min</sub> )       | 100°C                   | 150°C            |
| - Temperature Max (Ts <sub>max</sub> )       | 150°C                   | 200°C            |
| - Time (min to max) (ts)                     | 60 to 120 sec           | 60 to 180 sec    |
| Tsmax to T∟                                  |                         |                  |
| - Ramp-up Rate                               | <3°C/sec                | <3°C/sec         |
| Time maintained above:                       |                         |                  |
| - Temperature (T∟)                           | 183°C                   | 217°C            |
| - Time (t <sub>L</sub> )                     | 60 to 150 sec           | 60 to 150 sec    |
| Peak Temperature (T <sub>P</sub> )           | 240°C +0/-5°C           | 260°C +0/-5°C    |
| Time within 5°C of actual Peak               | 10 to 30 sec            | 20 to 40 sec     |
| Temperature (t <sub>P</sub> )                | 10 10 00 300            | 2010 40 300      |
| Ramp-down Rate                               | <6°C/sec                | <6°C/sec         |
| Time 25°C to Peak Temperature                | <6 minutes              | <8 minutes       |

#### 3. Flow (wave) soldering (solder dipping)

| Products         | Peak Temperature | Dipping Time |
|------------------|------------------|--------------|
| Pb devices.      | 245°C ±5°C       | 5sec ±1sec   |
| Pb-Free devices. | 260°C +0/-5°C    | 5sec ±1sec   |



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